

UPDATED 11/01/2007

14.40-15.40GHz 4-Watt Internally-Matched Power FET

FEATURES

- 14.40 -15.40GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +36.0 dBm Output Power at 1dB Compression
- 5.0 dB Power Gain at 1dB Compression
- 25% Power Added Efficiency
- -43 dBc IM3 at Po = 25.0 dBm SCL
- 100% Tested for DC, RF, and R_{TH}



ELECTRICAL CHARACTERISTICS (Ta = 25°C)



Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS ¹		TYP	MAX	UNITS
P _{1dB}	Output Power at 1dB Compression $f = 14.40-15.40GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1100\text{mA}$	35.5	36.0		dBm
G _{1dB}	Gain at 1dB Compression $f = 14.40-15.40GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1100\text{mA}$	4.5	5.0		dB
ΔG	Gain Flatness $f = 14.40-15.40GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 1100\text{mA}$			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 11000 \text{mA}$ f = 14.40-15.40GHz		25		%
Id _{1dB}	Drain Current at 1dB Compression f = 14.40-15.40GHz		1100	1400	mA
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; Pout = 25.0 dBm S.C.L ² V_{DS} = 10 V, $I_{DSQ} \approx 65\%$ IDSS f = 15.40GHz	-40	-43		dBc
I _{DSS}	Saturated Drain Current $V_{DS} = 3 \text{ V}, V_{GS} = 0 \text{ V}$		2080	2880	mA
V _P	Pinch-off Voltage $V_{DS} = 3 \text{ V}, I_{DS} = 20 \text{ mA}$		-2.5	-4.0	V
R _{TH}	Thermal Resistance ³		5.5	6.0	°C/W

Note: 1. Tested with 100 Ohm gate resistor.

2. S.C.L. = Single Carrier Level.

3. Overall Rth depends on case mounting.

ABSOLUTE MAXIMUM RATING FOR EFD

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²	
Vds	Drain-Source Voltage	15V	10V	
Vgs	Gate-Source Voltage	-5V	-4V	
lgf	Forward Gate Current	48mA	14.4mA	
lgr	Reverse Gate Current	-9.6mA	-2.4mA	
Pin	Input Power	35.5dBm	@ 3dB Compression	
Tch	Channel Temperature	175C	175C	
Tstg	Storage Temperature	-65C to +175C	-65C to +175C	
Pt	Total Power Dissipation	25W	25W	

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.



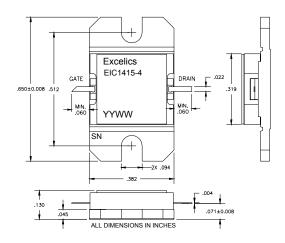
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PACKAGES OUTLINE

Dimensions in inches, Tolerance ± .005 unless otherwise specified

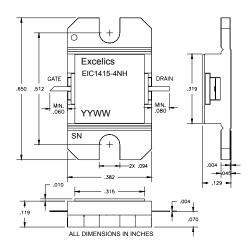
EIC1415-4 (Hermetic)





Caution! ESD sensitive device.

EIC1415-4NH (Non-Hermetic)





Caution! ESD sensitive device.

ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC1415-4	Hermetic	Industrial	14.40-15.40GHz	35.5	-40
EIC1415-4NH	Non-Hermetic	Industrial	14.40-15.40GHz	35.5	-40

Notes:

- 1. Contact factory for military and hi-rel grades.
- 2. Exact test conditions are specified in "Electrical Characteristics" table.

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